

NPN Silicon Transistor BUT11AF

High Voltage Power Switching Applications

MAXIMUM RATINGS ($T_C = 25^{\circ}C$ unless otherwise noted)

Symbol	Parameter	Value	Unit
V _{CBO}	Collector-Base Voltage	1000	V
V _{CEO}	Collector–Emitter Voltage	450	V
V _{EBO}	Emitter-Base Voltage	9	V
I _C	Collector Current (DC)	5	Α
I _{CP}	*Collector Current (Pulse)	10	Α
Ι _Β	Base Current (DC)	2	Α
I _{BP}	*Base Current (Pulse)	4	Α
PC	Collector Dissipation (T _C = 25°C)	40	W
TJ	Junction Temperature	150	°C
T _{STG}	Storage Temperature	-65~150	°C

Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.

THERMAL CHARACTERISTICS (T_C = 25°C, unless otherwise noted)

Symbol	Parameter	Max	Unit
$R_{\theta JC}$	Thermal Resistance, Junction to Case	3.125	°C/W

- 1. Base
- 2. Collector
- 3. Emitter

TO-220 Fullpack, 3-Lead CASE 221AT

MARKING DIAGRAM

BUT11A F AYWWZZ

BUT11AF = Specific Device Code

A = Site Code
Y = Year
WW = Work Week
ZZ = Assembly Lot Code

ORDERING INFORMATION

Device	Package	Shipping
BUT11AFTU	TO-220 Fullpack (Pb-Free)	1000 Units / Tube

ELECTRICAL CHARACTERISTICS (T_C = 25°C unless otherwise noted)

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
V _{CEO} (sus)	*Collector–Emitter Sustaining Voltage	$I_C = 100 \text{ mA}, I_B = 0$	450	-	-	V
I _{CES}	Collector Cut-off Current	V _{CE} = 1000 V, V _{BE} = 0	_	-	1	mA
I _{EBO}	Emitter Cut-off Current	V _{BE} = 9 V, I _C = 0	_	_	10	mA
V _{CE} (sat)	Collector-Emitter Saturation Voltage	$I_C = 2.5 \text{ A}, I_B = 0.5 \text{ A}$	_	_	1.5	V
V _{BE} (sat)	Base-Emitter Saturation Voltage	$I_C = 2.5 \text{ A}, I_B = 0.5 \text{ A}$	_	_	1.3	V
t _{ON}	Turn On Time	V _{CC} = 250 V, I _C = 2.5 A,	_	_	1	μS
t _{STG}	Storage Time	$I_{B1} = -I_{B2} = 0.5 \text{ A}, R_L = 100 \Omega$	_	_	4	μS
t _F	Fall Time		_	_	0.8	μS

Product parametric performance is indicated in the Electrical Characteristics for the listed test conditions, unless otherwise noted. Product performance may not be indicated by the Electrical Characteristics if operated under different conditions.

^{*}Pulsed: pulsed duration = 300 µs, duty cycle = 1.5%

BUT11AF

TYPICAL CHARACTERISTICS

Ic, COLLECTOR CURRENT (A)

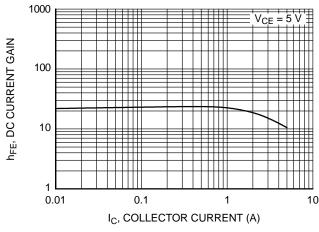


Figure 1. DC Current Gain

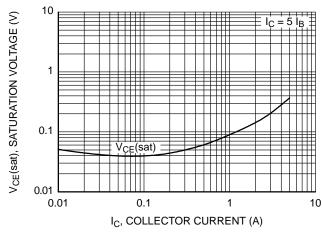


Figure 2. Collector-Emitter Saturation Voltage

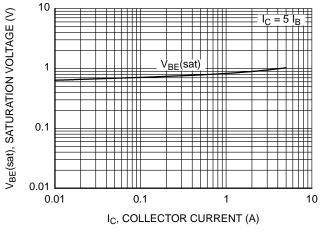


Figure 3. Base-Emitter Saturation Voltage

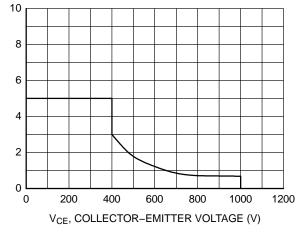


Figure 4. Reverse Biased Safe Operating Area

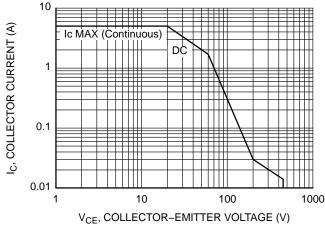


Figure 5. Safe Operating Area

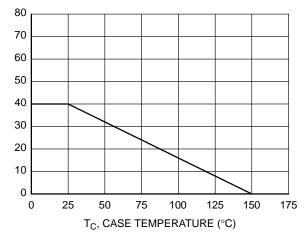
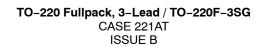


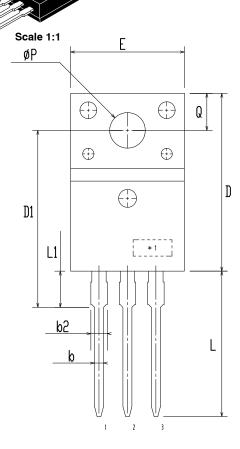
Figure 6. Power Derating

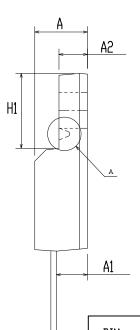
P_C, POWER DISSIPATION) (W)

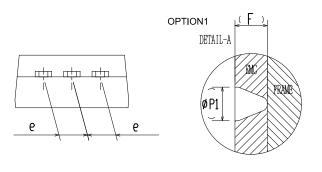




DATE 19 JAN 2021







l DIM	HILLIHITEKS				
ויונע	MIN	NDM	MAX		
Α	4.50	4.70	4.90		
A1	2.56	2.76	2.96		
A2	2.34	2.54	2.74		
b	0.70	0.80	0.90		
b2	~	2	1.47		
С	0.45	0.50	0.60		
D	15.67	15.87	16.07		
D1	15.60	15.80	16.00		
E	9.96	10.16	10.36		
е	2.34	2.54	2.74		
F	~	0.84	2		
H1	6.48	6.68	6.88		
L	12.78	12.98	13.18		
L1	3.03	3.23	3.43		
ØΡ	2.98	3.18	3,38		
ø P1	~	1.00	~		
Q	3,20	3.30	3.40		

MILL IMITERS

NOTES:

- A. DIMENSION AND TOLERANCE AS ASME Y14.5-2009
- B. DIMENSIONS ARE EXCLUSIVE OF BURRS, MOLD FLASH AND TIE BAR PROTRUCSIONS.

C

C. OPTION 1 - WITH SUPPORT PIN HOLE OPTION 2 - NO SUPPORT PIN HOLE

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DESCRIPTION:	TO-220 FULLPACK, 3-LEAD / TO-220F-3SG		PAGE 1 OF 1	

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